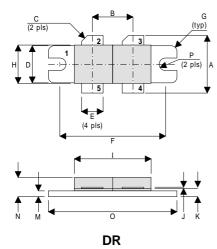


D1040UK

METAL GATE RF SILICON FET

MECHANICAL DATA



PIN 1 SOURCE (COMMON) **DRAIN 1** PIN₂ PIN₃ DRAIN 2 PIN 4 GATE 2 PIN 5 GATE 1

DIM	Millimetres	Tol.	Inches	Tol.
Α	19.05	0.50	0.75	0.020
В	10.77	0.13	0.424	0.005
С	45°	5°	45°	5°
D	9.78	0.13	0.385	0.005
E	5.71	0.13	0.225	0.005
F	27.94	0.13	1.100	0.005
G	1.52R	0.13	0.060R	0.005
Н	10.16	0.13	0.400	0.005
1	22.22	MAX	0.875	MAX
J	0.13	0.02	0.005	0.001
K	2.72	0.13	0.107	0.005
М	1.70	0.13	0.067	0.005
N	5.08	0.50	0.200	0.020
0	34.03	0.13	1.340	0.005
Р	1.61R	0.08	0.064R	0.003

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 400W - 28V - 108MHz**PUSH-PULL**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 16 dB MINIMUM

APPLICATIONS

VHF FM COMMUNICATIONS

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

$\overline{P_D}$	Power Dissipation	438W
BV_DSS	Drain – Source Breakdown Voltage *	70V
BV_GSS	Gate – Source Breakdown Voltage *	±20V
I _{D(sat)}	Drain Current *	35A
T _{stg}	Storage Temperature	−65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

^{*} Per Side

Semelab PIc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit
PER SIDE							
BV _{DSS}	Drain-Source Breakdown	V _{GS} = 0	I _D = 100mA	70			V
	Voltage	VGS - 0		70			'
	Zero Gate Voltage	\/ _ 20\/	V _{GS} = 0			7	m ^
DSS	Drain Current	$V_{DS} = 28V$				/	mA
I _{GSS}	Gate Leakage Current	V _{GS} = 20V	V _{DS} = 0			7	μА
V _{GS(th)}	Gate Threshold Voltage*	I _D = 10mA	$V_{DS} = V_{GS}$	1		7	V
9 _{fs}	Forward Transconductance*	V _{DS} = 10V	I _D = 7A	5.6			S
TOTAL DEVICE							
G _{PS}	Common Source Power Gain	P _O = 400W		16			dB
η	Drain Efficiency	V _{DS} = 28V	I _{DQ} = 2A	65			%
VSWR	Load Mismatch Tolerance	f = 108MHz		20:1			_
PER SIDE							
C _{iss}	Input Capacitance	V _{DS} = 28V V	$f_{GS} = -5V$ $f = 1MHz$			380	pF
C _{oss}	Output Capacitance	V _{DS} = 28V V	$f_{GS} = 0$ $f = 1MHz$			180	pF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 28V V	f = 0 $f = 1MHz$			10	pF

^{*} Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

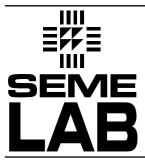
R _{THj-case}	Thermal Resistance Junction – Case	Max. 0.4°C / W
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Website: http://www.semelab.co.uk





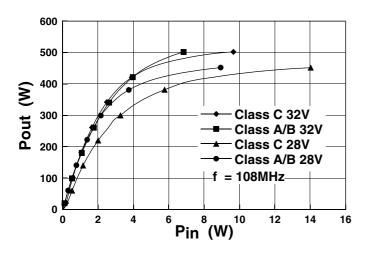


Figure 1
Output Power vs. Input Power

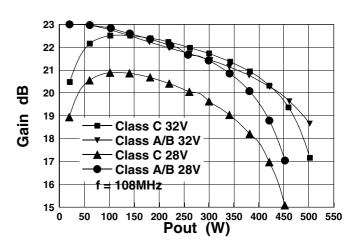


Figure 2
Gain vs. Output Power

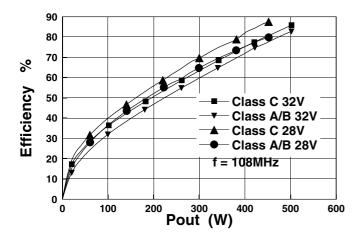


Figure 3
Efficiency vs. Output Power

OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency	Z _S	Z _L
MHz	Ω	Ω
108	1.5 + j3.5	1.5 - j0.4

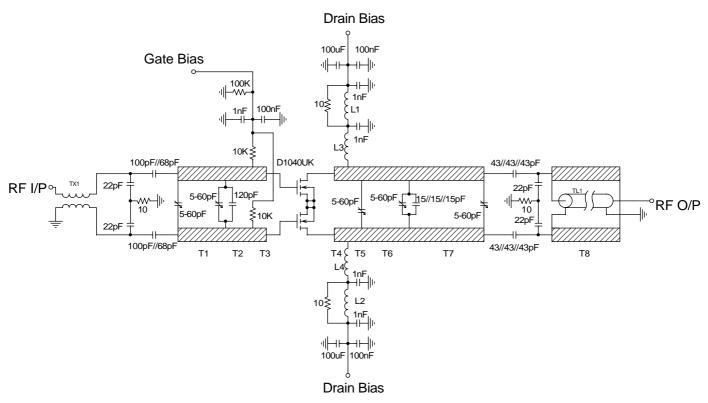
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D1040UK 108MHz Test Fixture

Substrate 1.6mm PTFE/glass ε_r =2.2

TX1	4 turns 500	coaxial ca	able wound	around toroid
1/\1	T (01110 0022	OUGNIGI OC	ADIC WOULIG	around toroid

TL1 160mm UT85 semi-rigid coax

L1, L2 1 turn 1.2mm dia wire on Siemens B62152A1X1 2 hole core

L3, L4 4 turns 1.2mm dia wire, 10mm internal dia

T8 4.8mm wide, all other lines 6mm wide

T1	50mm
T2	40mm
T3	10mm
T4	14mm
T5	8mm
T6	40mm
T7	66mm
T8	160mm

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